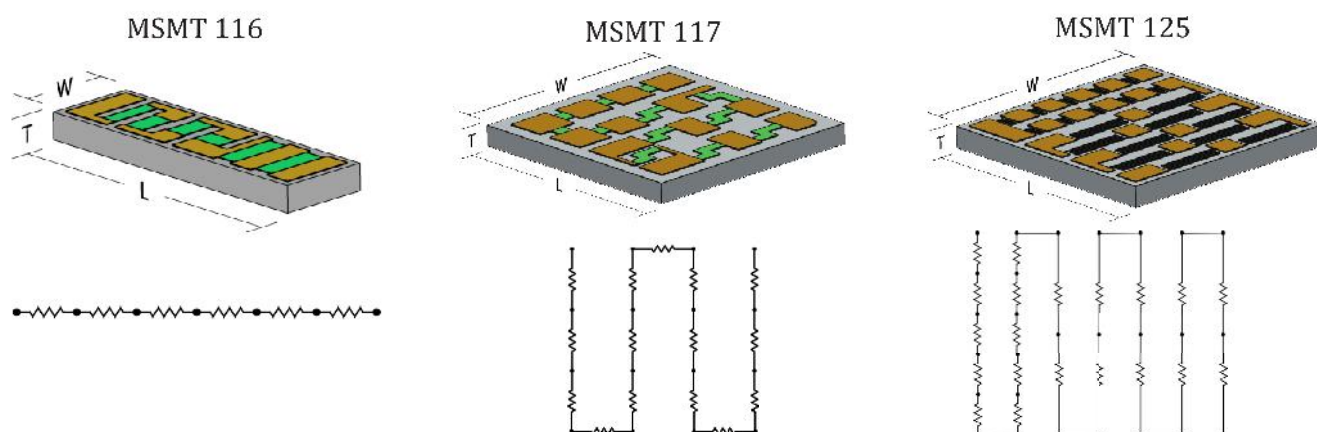


# MULTI-TAP RESISTORS



Mini-Systems, Inc. **MSMT** series chip Multi-Tap resistor arrays provide the design engineer a wide range of resistance values on a single chip. These chips are often used in circuits where **precision adjustments** are required. Connection to associated circuitry is accomplished using wire bonding. The MSMT series offers **high stability, low noise, and low T.C.R.** of Mini-Systems, Inc. proven thin film technology.

## RESISTANCE DISTRIBUTION

MSMT116*	(R1 = R2 = Rt / 24), (R3 = Rt / 12), (R4 = R5 = Rt / 4.8), (R6 = Rt / 2.4)
MSMT117*	(R1 to R7 = Rt / 8), (R8 to R12 = Rt / 40)
MSMT125*	(R1 to R10 = Rt / 110), (R11 to R20 = Rt / 11)

Rt = Total Resistance

\*= Individual values are by design

## DIMENSIONS

CASE SIZE	STYLE	TYPE	DIMENSIONS			RESISTANCE RANGE <sup>2</sup>		POWER RATING <sup>1</sup>
			L (±0.003") [±0.076mm]	W (±0.003") [±0.076mm]	T (±0.002") [±0.051mm]	Silicon	Alumina	
0602	MSMT	116	0.057" [1.448]	0.017" [0.432]	0.010" [0.254]	80Ω to 2kΩ	80Ω to 2kΩ	125mW
0303	MSMT	117	0.030" [0.762]	0.030" [0.762]	0.010" [0.254]	80Ω to 240kΩ	80Ω to 50kΩ	250mW
0303	MSMT	125	0.034" [0.864]	0.034" [0.864]	0.010" [0.254]	550Ω to 500kΩ	80Ω to 50kΩ	250mW

<sup>1</sup> Power Rating at 70°C Derated Linearly to 0% at 150°C

<sup>2</sup> Total Resistance

## PART NUMBER DESIGNATION

MSMT	—	125	—	S	T	—	550R0	K	—	G
STYLE		TYPE		SUBSTRATE	RESISTOR FILM		OHMIC VALUE	TOLERANCE		OPTION
MSMT		116		S = Silicon	T = Tantalum Nitride		<b>5-Digit Number:</b> 1st 4 digits are significant with "R" as decimal point when required. 5th digit represents number of zeros.	J = ±5% K = ±10%		G = Gold Bond Pads E = Aluminum Pads GB = Gold Backside
		117		A = Alumina						
		125								

**EXAMPLE: MSMT-125-ST-550R0K-G**

MSMT-125 Series, Silicon, Tantalum Nitride, 550Ω, ±10% Tol., Gold Bond Pads, Bare Backside



## THIN FILM DIVISION

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# MULTI-TAP RESISTORS

## GENERAL CHARACTERISTICS

Tolerance	±5% or ±10% (Applies to Total Resistance)
Current Noise	-30dB Max.
Voltage Rating	100V
Bond Pads	Gold (Standard), Aluminum (Optional)
Backside	Bare Substrate (Standard) Gold Back (Optional)
Operating Temperature	-55°C to +150°C
Storage Temperature	-65°C to +150°C

## SUBSTRATE CHARACTERISTICS

SUBSTRATE MATERIAL	Dielectric Constant @ 1MHz	Thermal Conductivity W/m•K
99.6% Alumina	9.9	28
Silicon (with 12kÅ SiO <sub>2</sub> )	N/A (SiO <sub>2</sub> 3.9)	149 (SiO <sub>2</sub> 1.38)

## RESISTOR CHARACTERISTICS

RESISTOR FILM	Passivation	TCR
Tantalum Nitride	Ta <sub>2</sub> O <sub>5</sub> (Self Passivating)	±150 ppm/°C

## PERFORMANCE SPECIFICATIONS

PROPERTY	TEST CONDITION	REQUIRED LIMITS	MSI TYPICAL LIMITS
SHORT TERM OVERLOAD	2.5xWVDC(6.25xRATED POWER)MIL-PRF-55342, +25°C, 5 SEC	±0.25 MAX ΔR/R	±0.10 MAX ΔR/R
HIGH TEMP EXPOSURE	+150°C, 100HRS	±0.20 MAX ΔR/R	±0.03 MAX ΔR/R
THERMAL SHOCK	MIL-STD 202, METHOD 107	±0.25 MAX ΔR/R	±0.10 MAX ΔR/R
MOISTURE RESISTANCE	MIL-STD 202, METHOD 106	±0.40 MAX ΔR/R	±0.10 MAX ΔR/R
STABILITY	MIL-STD 202 METHOD 108, 2000 HRS, +70°C, RATED POWER	±0.50 MAX ΔR/R	±0.10 MAX ΔR/R

All MSMT Series parts are produced on the same manufacturing line using the same materials and processes as parts manufactured to MIL-PRF-55342